

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	((YASUHITO) near2 (URASHIMA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/12/14 00:10
L3	1	(substrate and buffer adj layer and non \$1periodical\$2 and (groove or scratch)). clm.	US-PGPUB; USPAT	OR	ON	2010/12/14 00:15
S1	1	"10586543"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/01 16:30
S2	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/23 23:54
S3	0	("(insularnear2crystal)with(III\$1Vor (groupnearIIInearnitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:05
S4	1	(insular near2 crystal) with (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:06
S5	6	(insular near2 crystal) and (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:06
S6	0	(10/443794).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:08
S7	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:08

S8	4	("2000068474").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:08
S9	513	(III\$1V or (group near III near nitride)) and (groove same surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:22
S10	0	S9 and (buffer near (column\$2 island))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:23
S11	2	S9 and (substrate with surface with roughness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/24 00:46
S12	19	(udagawa near takashi).in. and (epitaxial near wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/28 20:14
S13	18	("5103284" "5455431").PN. OR ("5886367").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/28 20:17
S14	0	("("20030207125").PN.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/28 20:35
S15	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/28 20:35
S16	96964	(III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 13:28
S17	13014	S16 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 13:29

S18	477	S17 and (substrate with surface with (roughness rough))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 13:30
S19	216	S18 and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 13:31
S20	33	("20030064535" "20040235268" "20050032330" "5013681" "5217564" "5231047" "5374564" "5391257" "5637187" "5641381" "5713057" "5877070" "5882987" "6020252" "6103597" "6150239" "6221738" "6242324" "6323108" "6328796" "6346458" "6429104" "6465327" "6497763" "6504091" "6794276" "6815309" "6908828"). PN. OR ("7019339").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/29 16:58
S21	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/29 17:10
S24	269	(III\$1V or (group near III near nitride)) and (groove with surface with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 18:59
S25	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 19:42
S26	357	(III\$1V or (group near III near nitride)) and (groove near4 substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 20:02
S27	13	("4567393" "5571603").PN. OR ("5821568").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/29 20:19

S28	11	("5821568" "5909036" "6072197" "6086673" "6107162" "6225650" "6335546" "6411636" "6542526" "6576533").PN. OR ("6773504").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/29 20:21
S29	342	(III\$1V or (group near III near nitride)) and (surface with (roughness irregularities) with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 20:31
S30	328	S29 not (S26 or S24)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 20:32
S31	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 21:02
S32	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/29 21:05
S33	42	(III\$1V or (group near III near nitride)) and (groove with surface with substrate with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/29 21:12
S34	51	(III\$1V or (group near III near nitride)) and ((groove near4 substrate) with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/31 23:01
S35	5	("4308078" "6071795" "6113685" "6348096" "6426519").PN. OR ("6864158").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/31 23:08
S36	39	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 14:59

S37	7	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire same depth) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 15:04
S38	18	(III\$1V or (group near III near nitride)) and (groove same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 15:04
S39	5	(III\$1V or (group near III near nitride)) and (roughness same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 15:14
S40	3	(III\$1V or (group near III near nitride)) and (buffer near4 columnar) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 16:20
S41	2	("6376866").PN. OR ("6917059").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/01 18:06
S42	168	257/11.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:56
S43	284	257/189.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:57
S44	309	257/615.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:57
S45	3	257/e33.023.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:57
S46	352	257/e33.049.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:57

S47	31	257/e31.019.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/01 18:57
S48	1	"10586543"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/29 18:14
S49	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S50	0	("(insularnear2crystal)with(III\$1Vor (groupnearIIInearnitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S51	1	(insular near2 crystal) with (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S52	6	(insular near2 crystal) and (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S53	0	(10/443794).OCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S54	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S55	4	("2000068474").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14

S56	513	(III\$1V or (group near III near nitride)) and (groove same surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S57	0	S56 and (buffer near (column\$2 island))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S58	2	S56 and (substrate with surface with roughness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S59	19	(udagawa near takashi).in. and (epitaxial near wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S60	18	("5103284" "5455431").PN. OR ("5886367").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S61	0	("("20030207125").PN.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S62	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S63	99489	(III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S64	13993	S63 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S65	510	S64 and (substrate with surface with (roughness rough))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14

S66	217	S65 and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S67	34	("20030064535" "20040235268" "20050032330" "5013681" "5217564" "5231047" "5374564" "5391257" "5637187" "5641381" "5713057" "5877070" "5882987" "6020252" "6103597" "6150239" "6221738" "6242324" "6323108" "6328796" "6346458" "6429104" "6465327" "6497763" "6504091" "6794276" "6815309" "6908828"). PN. OR ("7019339").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S68	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S69	269	(III\$1V or (group near III near nitride)) and (groove with surface with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S70	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S71	357	(III\$1V or (group near III near nitride)) and (groove near4 substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S72	14	("4567393" "5571603").PN. OR ("5821568").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S73	11	("5821568" "5909036" "6072197" "6086673" "6107162" "6225650" "6335546" "6411636" "6542526" "6576533").PN. OR ("6773504").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14

S74	343	(III\$1V or (group near III near nitride)) and (surface with (roughness irregularities) with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S75	329	S74 not (S71 or S69)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S76	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S77	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S78	42	(III\$1V or (group near III near nitride)) and (groove with surface with substrate with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S79	51	(III\$1V or (group near III near nitride)) and ((groove near4 substrate) with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S80	5	("4308078" "6071795" "6113685" "6348096" "6426519").PN. OR ("6864158").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S81	39	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14

S82	7	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire same depth) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S83	18	(III\$1V or (group near III near nitride)) and (groove same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S84	5	(III\$1V or (group near III near nitride)) and (roughness same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S85	3	(III\$1V or (group near III near nitride)) and (buffer near4 columnar) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S86	3	("6376866").PN. OR ("6917059").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/29 18:14
S87	168	257/11.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S88	285	257/189.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S89	310	257/615.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S90	3	257/e33.023.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S91	352	257/e33.049.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14

S92	32	257/e31.019.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/29 18:14
S93	1	"10586543"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/01 00:50
S94	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S95	0	("(insularnear2crystal)with(III\$1Vor (groupnearIIInearnitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S96	1	(insular near2 crystal) with (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S97	6	(insular near2 crystal) and (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S98	0	(10/443794).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S99	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S100	4	("2000068474").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S101	513	(III\$1V or (group near III near nitride)) and (groove same surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S102	0	S101 and (buffer near (column\$2 island))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S103	2	S101 and (substrate with surface with roughness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S104	19	(udagawa near takashi).in. and (epitaxial near wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S105	18	("5103284" "5455431").PN. OR ("5886367").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S106	0	("("20030207125").PN.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S107	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S108	99553	(III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S109	14012	S108 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S110	511	S109 and (substrate with surface with (roughness rough))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S111	217	S110 and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S112	34	("20030064535" "20040235268" "20050032330" "5013681" "5217564" "5231047" "5374564" "5391257" "5637187" "5641381" "5713057" "5877070" "5882987" "6020252" "6103597" "6150239" "6221738" "6242324" "6323108" "6328796" "6346458" "6429104" "6465327" "6497763" "6504091" "6794276" "6815309" "6908828"). PN. OR ("7019339").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S113	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S114	269	(III\$1V or (group near III near nitride)) and (groove with surface with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S115	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S116	357	(III\$1V or (group near III near nitride)) and (groove near4 substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S117	14	("4567393" "5571603").PN. OR ("5821568").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S118	11	("5821568" "5909036" "6072197" "6086673" "6107162" "6225650" "6335546" "6411636" "6542526" "6576533").PN. OR ("6773504").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50

S119	343	(III\$1V or (group near III near nitride)) and (surface with (roughness irregularities) with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S120	329	S119 not (S116 or S114)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S121	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S122	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S123	42	(III\$1V or (group near III near nitride)) and (groove with surface with substrate with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S124	51	(III\$1V or (group near III near nitride)) and ((groove near4 substrate) with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S125	5	("4308078" "6071795" "6113685" "6348096" "6426519").PN. OR ("6864158").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S126	39	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S127	7	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire same depth) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S128	18	(III\$1V or (group near III near nitride)) and (groove same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S129	5	(III\$1V or (group near III near nitride)) and (roughness same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S130	3	(III\$1V or (group near III near nitride)) and (buffer near4 columnar) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S131	3	("6376866").PN. OR ("6917059").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S132	168	257/11.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S133	285	257/189.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S134	310	257/615.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S135	3	257/e33.023.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S136	352	257/e33.049.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S137	32	257/e31.019.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S138	1	"10586543"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/01 00:50
S139	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S140	0	("(insularnear2crystal)with(III\$1Vor (groupnearIIInearnitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S141	1	(insular near2 crystal) with (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S142	6	(insular near2 crystal) and (III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S143	0	(10/443794).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S144	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S145	4	("2000068474").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S146	513	(III\$1V or (group near III near nitride)) and (groove same surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S147	0	S146 and (buffer near (column\$2 island))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S148	2	S146 and (substrate with surface with roughness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S149	19	(udagawa near takashi).in. and (epitaxial near wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S150	18	("5103284" "5455431").PN. OR ("5886367").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S151	0	("("20030207125").PN.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S152	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S153	99553	(III\$1V or (group near III near nitride))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S154	14012	S153 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S155	511	S154 and (substrate with surface with (roughness rough))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S156	217	S155 and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S157	34	("20030064535" "20040235268" "20050032330" "5013681" "5217564" "5231047" "5374564" "5391257" "5637187" "5641381" "5713057" "5877070" "5882987" "6020252" "6103597" "6150239" "6221738" "6242324" "6323108" "6328796" "6346458" "6429104" "6465327" "6497763" "6504091" "6794276" "6815309" "6908828"). PN. OR ("7019339").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S158	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S159	269	(III\$1V or (group near III near nitride)) and (groove with surface with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S160	1	10/443794	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S161	357	(III\$1V or (group near III near nitride)) and (groove near4 substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S162	14	("4567393" "5571603").PN. OR ("5821568").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S163	11	("5821568" "5909036" "6072197" "6086673" "6107162" "6225650" "6335546" "6411636" "6542526" "6576533").PN. OR ("6773504").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50

S164	343	(III\$1V or (group near III near nitride)) and (surface with (roughness irregularities) with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S165	329	S164 not (S161 or S159)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S166	2	("20030207125").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S167	44	("3964957" "4495219" "4530149" "4906594" "5141878" "5198071" "5198371" "5213986" "5374564" "5409563" "5427052" "5494835" "5506176" "5508207" "5518965" "5559043" "5686980" "5705421" "5714395" "5841931" "5854123" "5869387" "5869405" "5877070" "5966620" "5966625" "5968279" "6004868" "6008128" "6107213" "6143628" "6162705" "6171965" "6171982" "6194327" "6204151" "6214701" "6251754" "6274464" "6287941" "6342436").PN. OR ("6969668").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S168	42	(III\$1V or (group near III near nitride)) and (groove with surface with substrate with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S169	51	(III\$1V or (group near III near nitride)) and ((groove near4 substrate) with (".mu.m " or "nm")) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S170	5	("4308078" "6071795" "6113685" "6348096" "6426519").PN. OR ("6864158").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S171	39	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S172	7	(III\$1V or (group near III near nitride)) and (groove same surface same substrate same sapphire same depth) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S173	18	(III\$1V or (group near III near nitride)) and (groove same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S174	5	(III\$1V or (group near III near nitride)) and (roughness same substrate same sapphire same (depth deep)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S175	3	(III\$1V or (group near III near nitride)) and (buffer near4 columnar) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S176	3	("6376866").PN. OR ("6917059").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/01 00:50
S177	168	257/11.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S178	285	257/189.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S179	310	257/615.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S180	3	257/e33.023.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S181	352	257/e33.049.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50

S182	32	257/e31.019.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/01/01 00:50
S183	1	"10586543"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:49
S184	0	S183 and scratch and strip\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:49
S185	0	S183 and scratch and stripe\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:50
S186	1	S183 and scratch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:50
S187	0	S183 and scratch and random	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:56
S188	1	S183 and scratch and roughness	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/12 14:56
S189	1547	"117"/\$3 and III-V	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 21:16
S190	533	(III\$1V or (group near III near nitride)) and ((groove scratch) same surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 21:17

S191	0	((III\$1V or (group near III near nitride)) and ((groove scratch) same surface same substrate same (non-periodic\$4 or nonperiodic\$4)) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 21:18
S192	1547	"117"/\$3 and III-V	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:08
S193	13	S192 and ((III\$1V or (group near III near nitride)) and ((groove scratch) near5 surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:08
S194	9	((YASUHITO) near2 (URASHIMA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/07/31 22:43
S195	13	S192 and ((groove scratch) near5 surface same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:46
S196	42	S192 and ((groove scratch) same substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:46
S197	0	((III\$1V or (group near III near nitride)) and ((groove near3 (non-periodic or ninperiodic)) with surface with substrate) and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:49
S198	8	("20020078881" "20030207125" "6864158" "6917059").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:51
S199	2	"20030207125"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 22:55
S200	327	257/51.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 23:25

S201	488	257/e21.108.ccls. and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/07/31 23:26
S202	0	(Group-III and nitride adj semiconductor and buffer adj layer and substrate and (columnar or island-like) and non-periodically and scratches and average adj depth).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/31 23:54
S203	4	("20020170489" "6232623").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/16 21:28
S204	0	(substrate near3 (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with (groove recess) with (non \$1periodic non\$1periodically)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 13:45
S205	1	(substrate near3 (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) same (groove recess) same (non \$1periodic non\$1periodically)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 13:45
S206	2	(substrate near3 (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) same (non\$1periodic non\$1periodically)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 13:47
S207	4	("20020170489" "6232623").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 13:49
S208	2	("20020170489" "6232623").PN.	US-PGPUB; USPAT	OR	ON	2010/08/17 13:49
S209	32	("5604763" "5919305").PN. OR ("6232623").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/08/17 13:57
S210	7	("20010019136" "6015979" "6030848" "6232623" "6408015").PN. OR ("6764871").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/08/17 14:08
S211	0	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with (groove recess) with (non \$1periodic non\$1periodically)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 14:28

S212	393	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with (groove recess)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 14:29
S213	608	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with (groove recess)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/17 14:29
S214	303	S213 and @ad<"20040126"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 14:31
S215	211	S213 and @ad<"20040126"	US-PGPUB; USPAT	OR	ON	2010/08/17 14:32
S216	12	("3400057" "3958554" "5976711" "6183874").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/17 16:07
S217	459	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with (rough roughness uneven unevenness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 16:15
S218	392	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with surface with (rough roughness uneven unevenness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 16:15
S219	392	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with surface with (rough roughness uneven unevenness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/17 18:29
S220	124	S219 and @ad<"20040126"	US-PGPUB; USPAT	OR	ON	2010/08/17 18:29
S221	6	("5154023" "5376224" "6197660").PN. OR ("6858537").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/08/17 19:50
S222	53	(substrate with (sapphire or "Al.sub.2O.sub.3" or silicon adj carbide or SiC)) with ((groove recess) near3 (thick thickness deep depth))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/18 12:05
S223	18	S222 and @ad<"20040126"	US-PGPUB; USPAT	OR	ON	2010/08/18 12:06

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